

**isc Silicon NPN Power Transistor**
**2SC3317**
**DESCRIPTION**

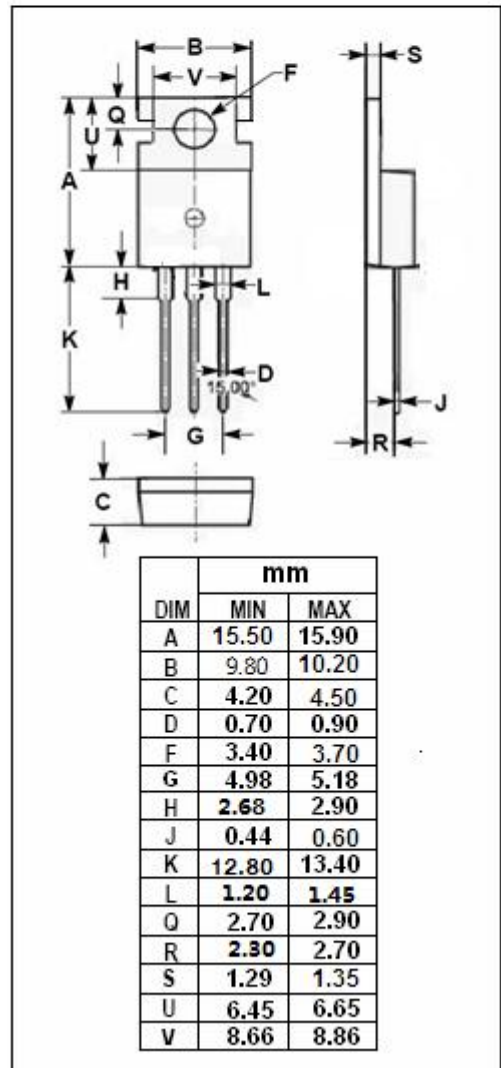
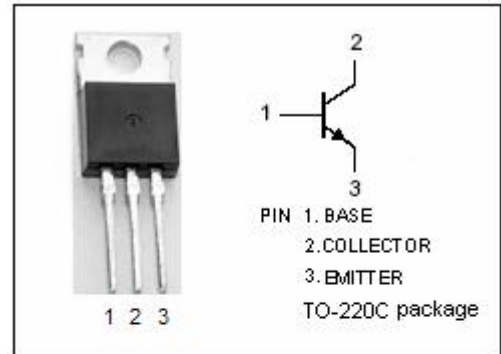
- Collector-Emitter Sustaining Voltage-  
:  $V_{CEO(SUS)} = 400V(\text{Min})$
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Switching regulators
- Ultrasonic generators
- High frequency inverters
- General purpose power amplifiers

**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	500	V
$V_{CEO}$	Collector-Emitter Voltage	400	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_C$	Collector Current-Continuous	5	A
$I_B$	Base Current-Continuous	0.5	A
$P_C$	Total Power Dissipation @ $T_a = 25^\circ\text{C}$	1.5	W
	Total Power Dissipation @ $T_c = 25^\circ\text{C}$	40	
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



## isc Silicon NPN Power Transistor

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## ELECTRICAL CHARACTERISTICS

T<sub>c</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA ; I <sub>B</sub> = 0	400		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA ; I <sub>E</sub> = 0	500		V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.4A		1.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.4A		1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 500V ; I <sub>E</sub> = 0		100	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7V; I <sub>C</sub> = 0		1.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.1A ; V <sub>CE</sub> = 5V	20		
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 2A ; V <sub>CE</sub> = 5V	10		
Switching times					
t <sub>r</sub>	Rise Time	V <sub>CC</sub> ≈ 200V, R <sub>L</sub> = 250 Ω , I <sub>B1</sub> = -I <sub>B2</sub> = 0.08A,		1.0	μ s
t <sub>stg</sub>	Storage Time			2.5	μ s
t <sub>f</sub>	Fall Time			1.0	μ s

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